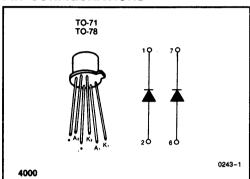
ID100, ID101 Dual Low Leakage Diode

GENERAL DESCRIPTION

The ID100 and ID101 are monolithic dual diodes intended for use in applications requiring extremely low leakage currents. Applications include interstage coupling with reverse isolation, signal clipping and clamping and protection of ultra low leakage FET differential dual and operational amplifi-

PIN CONFIGURATIONS



FEATURES

- I_R = 0.1pA (Typical)
- BV_R>30V
- Cras = 0.75pF (Typical)

ABSOLUTE MAXIMUM RATINGS

(T _A = 25°C unless otherwise noted)
Diode Reverse Voltage 30V
Diode to Diode Voltage ± 50V
Forward Current 20mA
Reverse Current 100 µA
Storage Temperature Range65°C to +200°C
Operating Temperature Range55°C to +150°C
Lead Temperature (Soldering, 10sec) + 300°C
Power Dissipation 300mW
Derate above 25°C 2.4mW/°C

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ORDERING INFORMATION

TO78	T071
ID100	ID101

ELECTRICAL CHARACTERISTICS (@ 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions		ID100, ID101			Units
				Min	Тур	Max	
V _F	Forward Voltage Drop	I _F =10mA		0.8		1.1	V
BVR	Reverse Breakdown Voltage	I _R = 1μA		30		-	٧
IR	I _R Reverse Leakage Current	V _R =1V			0.1		рA
		V _R = 10V			2.0	10	
			T _A =125°C			10	nA
I _{R1} -I _{R2}	Differential Leakage Current	V _R = 10V				3	pА
C _{rss}	Total Reverse Capacitance	V _R = 10V, f = 1Hz (Note 1)			0.75	1	pF

NOTE 1: For design reference only, not 100% tested.

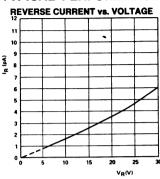
^{2:} Pins 3 and 5 should not be connected together nor connected to the circuit in any way.

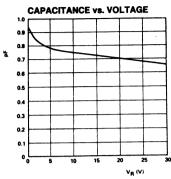
ID100, ID101



TYPICAL PERFORMANCE CHARACTERISTICS

0243-3





0243-4

